

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- Enhanced power dissipation capability of 1115 mW

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	5.6	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 25 °C		-	31	36	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D L
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G 017aaa253

# 6. Ordering information

Table 3.   Ordering information					
Type number	Package				
	Name	Description	Version		
PMV37EN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV37EN2	%К7

[1] % = placeholder for manufacturing site code

## 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

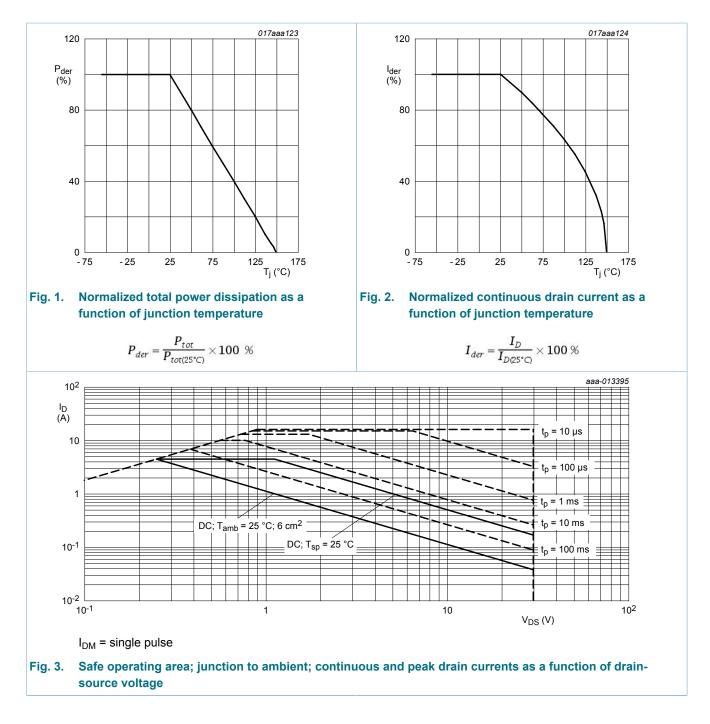
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	5.6	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	4.5	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.8	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	16	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	510	mW
			[1]	-	1115	mW
		T <sub>sp</sub> = 25 °C		-	5000	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
ls	source current	T <sub>amb</sub> = 25 °C	[1]	-	1	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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## 9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	209	246	K/W
			[2]	-	95	112	K/W
		in free air; t ≤ 5 s	[2]	-	63	72	K/W

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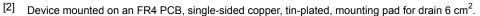
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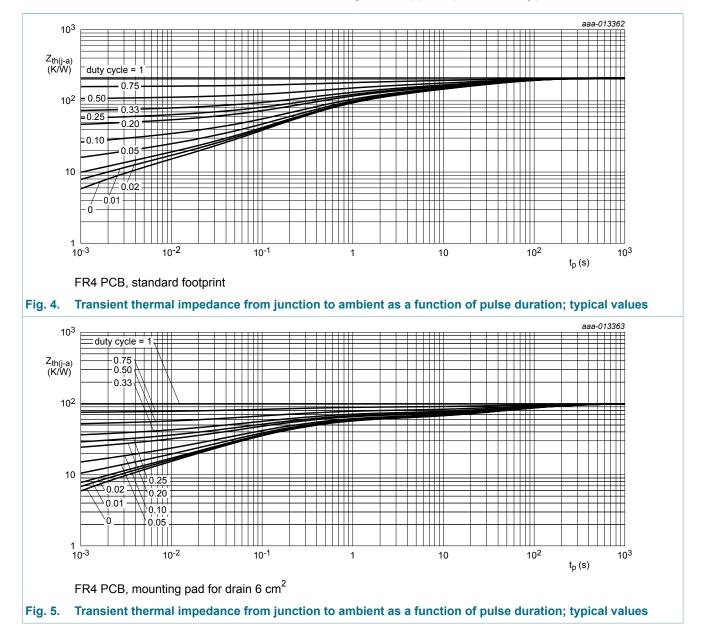
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	20	25	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



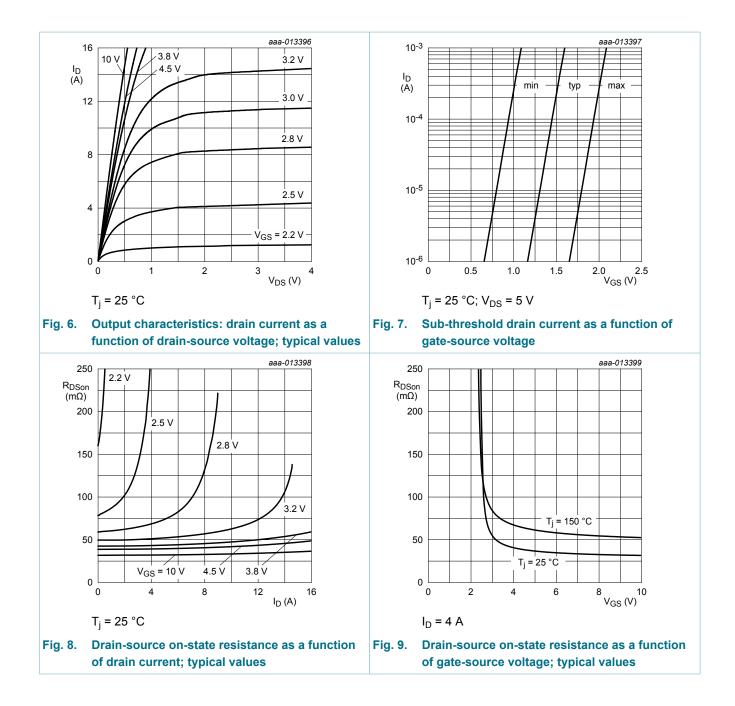


## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1	1.5	2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 25 °C	-	31	36	mΩ
resistance	resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 150 °C	-	48	56	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 3.9 A; T <sub>j</sub> = 25 °C	-	37	47	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	10	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	7	-	Ω
Dynamic cl	naracteristics		I.			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V;	-	3.6	6.3	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	209	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	50	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	17	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	11	-	ns
t <sub>f</sub>	fall time		-	2	-	ns
Source-dra	in diode		1	1		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.75	1.2	V

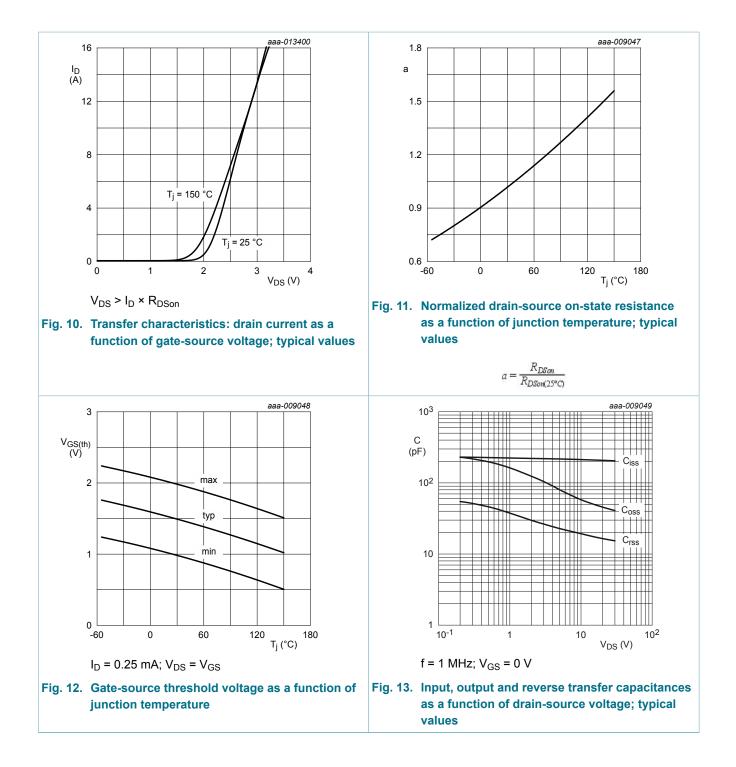
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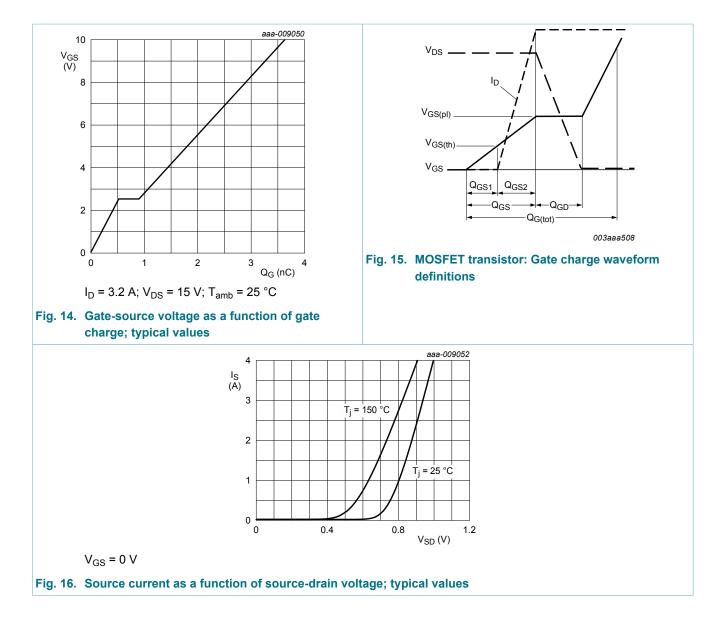
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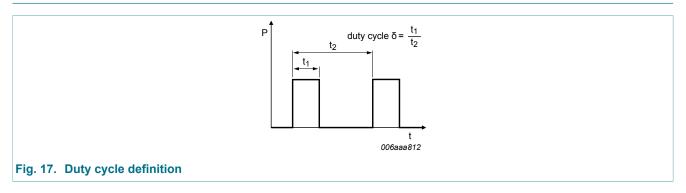


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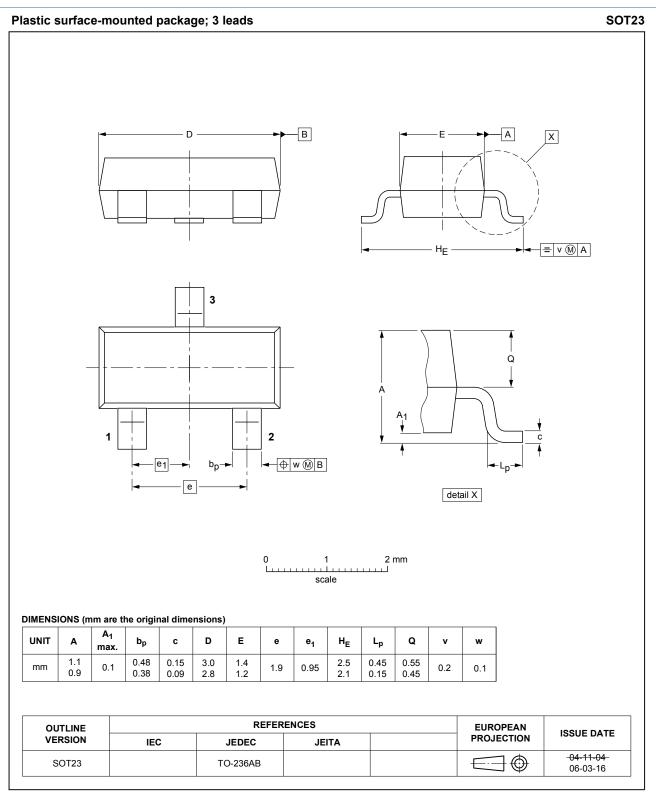


# **11. Test information**



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## 12. Package outline



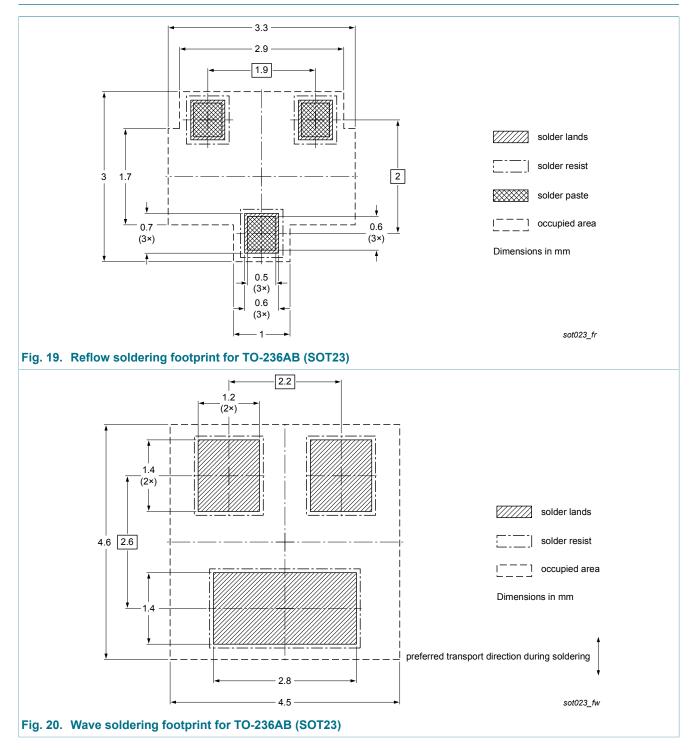
#### Fig. 18. Package outline TO-236AB (SOT23)

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## 13. Soldering



# 14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV37EN2 v.1	20140603	Product data sheet	-	-

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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